Dados trabalho anterior:

|  |  |  |  |
| --- | --- | --- | --- |
| TRANSÍSTOR | MODELO | W | L |
| NMOS1 | N\_12\_11hvt | 4 µ | 2 µ |
| NMOS2 | 1 µ | 0.5 µ |

|  |  |  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- |
|  | m | b | Is [A] | Vt0[V] | ɸ | 𝛾 | Kp | 𝚹 | β | Ut [V] |
| NMOS1 | -0.0182 | 0.0092 | 82.439e-06 | 0.5209 | 0.9650 | 0.4320 | 2.9495e-04 | -0.5353 | 1.4747e-04 | 0.025 |
| NMOS2 | -0.0116 | 0.0070 | 33.645e-06 | 0.5390 | 0.9320 | 0.4000 | 2.0008e-04 | -0.7240 | 1.0004e-04 | 0.025 |

|  |  |  |  |
| --- | --- | --- | --- |
| TRANSÍSTOR | MODELO | W | L |
| PMOS1 | P\_12\_11hvt | 4 µ | 2 µ |
| PMOS2 | 1 µ | 0.5 µ |

|  |  |  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- |
|  | m | b | Is [A] | Vt0[V] | ɸ | 𝛾 | Kp | 𝚹 | β | Ut [V] |
| PMOS1 | -0.0099 | 0.0053 | 2.4377e-07 | 0.5061 | 0.2240 | 0.3498 | 1.5639e-04 | -0.0369 | 7.8193e-05 | 0.025 |
| PMOS2 | -0.0101 | 0.0053 | 2.5629e-07 | 0.5060 | 0.2336 | 0.3449 | 1.5963e-04 | -0.0203 | 7.9815e-05 | 0.025 |